



# WE03-6R1N

## Transient Voltage Suppressor

### Features

- Solid-state silicon-avalanche technology
- Low operating and clamping voltage
- ESD Protection for super speed differential signaling channels
- Ultra low capacitance: 0.3pF typical(I/O to I/O)
- Low Leakage
- "feed through" layout

### IEC COMPATIBILITY (EN61000-4)

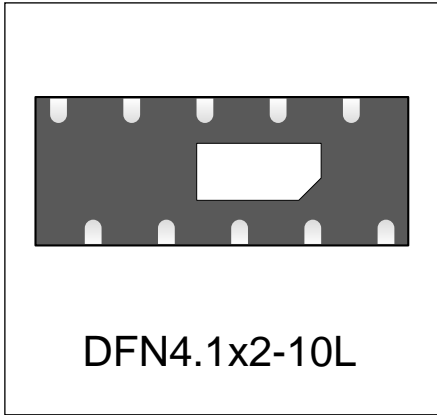
- IEC 61000-4-2 (ESD) ±22kV (air), ±22kV (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)

### Mechanical Characteristics

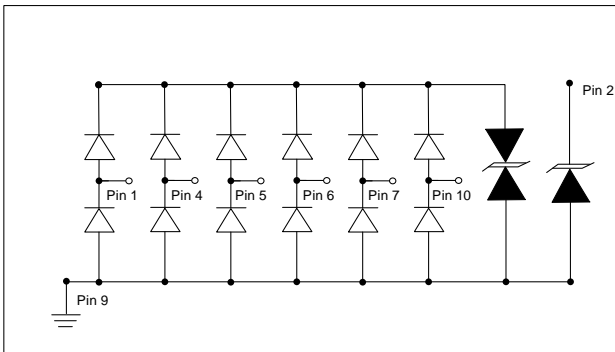
- DFN4.1x2-10L package
- Marking: Marking Code
- Packaging: Tape and Reel
- RoHS Compliant& HF

### Applications

- USB 3.0
- HDMI 1.4
- High speed port protection
- Portable electronics



### Circuit Diagram



### Schematic & PIN Configuration

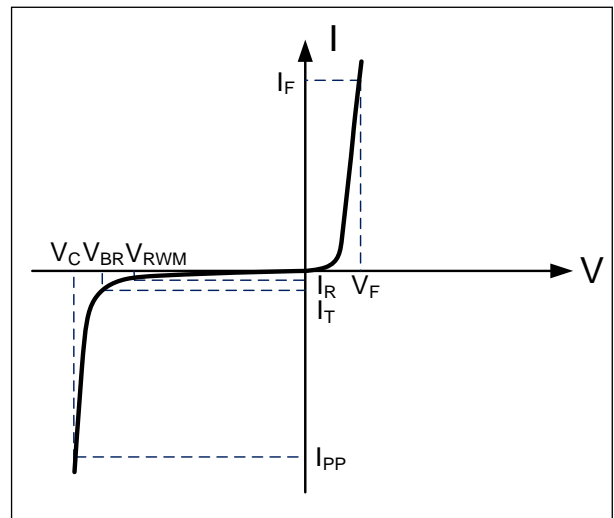
| Pin          | Identificaion |
|--------------|---------------|
| 1,4,5,6,7,10 | I/O Lines     |
| 2            | Vcc Line      |
| 9            | Ground        |
| 3,8          | NC            |

**Absolute Maximum Rating**

| Rating                                   | Symbol    | Value(Any I/O pin to Gnd) | Value(Vcc pin to Gnd) | Units |
|--|-----------|---------------------------|-----------------------|-------|
| Peak Pulse Power ( $t_p = 8/20\mu s$ )   | $P_{PP}$  | 50                        | 58.5                  | Watts |
| Peak Pulse Current ( $t_p = 8/20\mu s$ ) | $I_{pp}$  | 5                         | 4.5                   | A     |
| Operating Temperature                    | $T_J$     | -55 to + 125              | -55 to + 125          | °C    |
| Storage Temperature                      | $T_{STG}$ | -55 to +150               | -55 to +150           | °C    |

**Electrical Parameters**

| Symbol    | Parameter                           |
|-----------|-------------------------------------|
| $I_{PP}$  | Reverse Peak Pulse Current          |
| $V_C$     | Clamping Voltage @ $I_{PP}$         |
| $V_{RWM}$ | Reverse Stand-Off Voltage           |
| $I_R$     | Reverse Leakage Current @ $V_{RWM}$ |
| $V_{BR}$  | Breakdown Voltage @ $I_T$           |
| $I_T$     | Test Current                        |
| $I_F$     | Forward Current                     |
| $V_F$     | Forward Voltage @ $I_F$             |



**Electrical Characteristics(T=25°C unless otherwise noted)**

| Parameter                         | Symbol    | Conditions  | Minimum | Typical | Maximum | Units    |
|-----------------------------------|-----------|---|---------|---------|---------|----------|
| Reverse Stand-Off Voltage         | $V_{RWM}$ | Any I/O pin to ground                                   |         |         | 3.3     | V        |
|                                   |           | Vcc pin to ground                                       |         |         | 5.0     | V        |
| Reverse Breakdown Voltage         | $V_{BR}$  | $I_T = 1mA$<br>Any I/O pin to ground                    | 3.7     |         |         | V        |
|                                   |           | $I_T = 1mA$<br>Vcc pin to ground                        | 5.5     |         |         | V        |
| Reverse Leakage Current           | $I_R$     | $V_{RWM} = 3.3V$<br>Any I/O pin to ground               |         |         | 500     | nA       |
|                                   |           | $V_{RWM} = 5.0V$<br>Vcc pin to ground                   |         |         | 500     | nA       |
| Clamping Voltage                  | $V_C$     | $I_{pp} = 5A, t_p = 8/20\mu s$<br>Any I/O pin to ground |         | 8.5     | 10      | V        |
|                                   |           | $I_{pp} = 4.5A, t_p = 8/20\mu s$<br>Vcc pin to ground   |         | 11      | 13      | V        |
| Dynamic Resistance <sup>1,2</sup> | $R_{DYN}$ | TLP=0.2/100ns<br>Any I/O pin to ground                  |         | 0.38    |         | $\Omega$ |
|                                   |           | TLP=0.2/100ns<br>Vcc pin to ground                      |         | 0.39    |         | $\Omega$ |
| Junction Capacitance              | $C_j$     | $V_R = 0V, f = 1MHz$<br>I/O pin to GND                  |         | 0.56    | 0.8     | pF       |
|                                   |           | $V_R = 0V, f = 1MHz$<br>Vcc pin to ground               |         | 30      | 40      | pF       |

Notes : 1、 TLP Setting :  $t_p = 100ns, t_r = 0.2ns, I_{TLP}$  and  $V_{TLP}$  sample window:  $t_1 = 70ns$  to  $t_2 = 90ns$ .  
 2、 Dynamic resistance calculated from  $I_{PP} = 4A$  to  $I_{PP} = 16A$  using "Best Fit".

Figure 1: Peak Pulse Power vs. Pulse Time

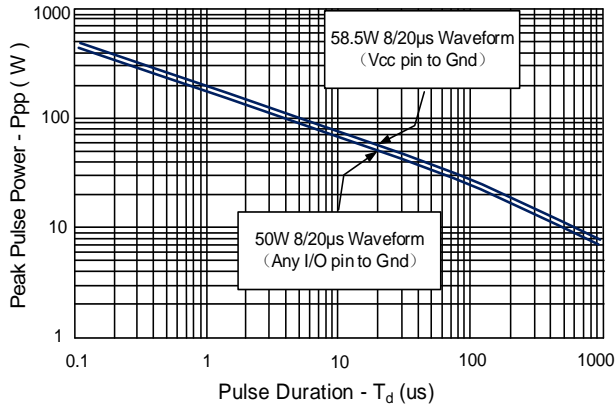


Figure 2: Power Derating Curve

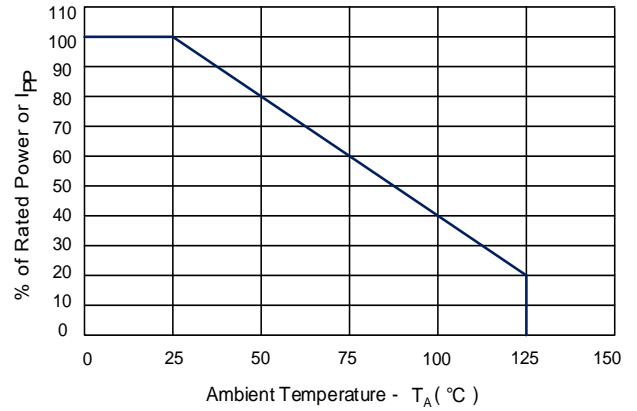


Figure 3: Clamping Voltage vs. Peak Pulse Current

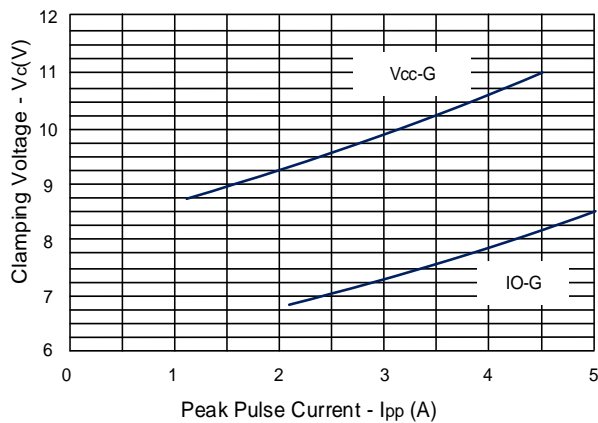


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

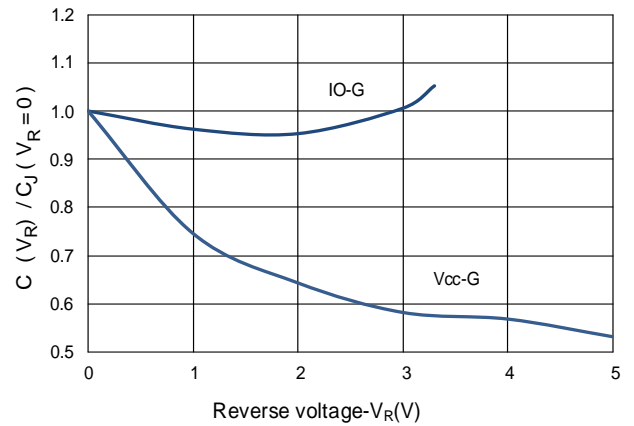


Figure 5: TLP I-V Curve (IO-G)

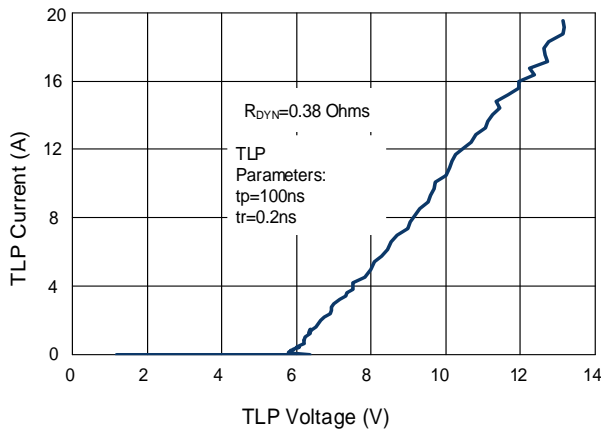
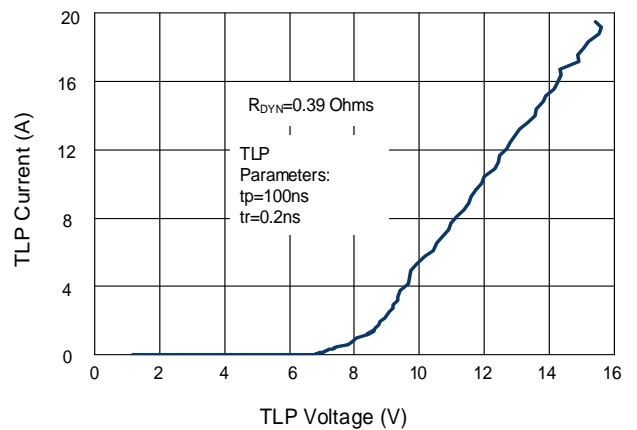
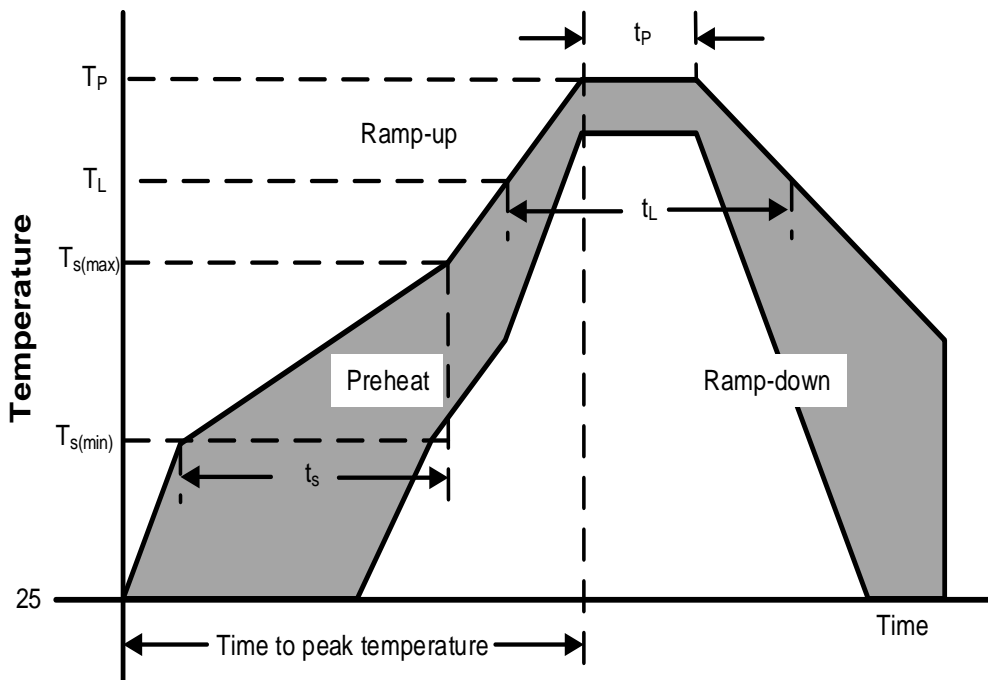


Figure 6: TLP I-V Curve (Vcc-G)



Soldering Parameters

| Reflow Condition                                       |                                  | Pb – Free assembly |
|--|----------------------------------|--------------------|
| Pre Heat   | Temperature Min ( $T_{s(min)}$ ) | 150°C              |
|  | Temperature Max ( $T_{s(max)}$ ) | 200°C              |
|  | Time (min to max) ( $t_s$ )      | 60 – 190 secs      |
| Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak |                                  | 5°C/second max     |
| $T_{s(max)}$ to $T_L$ —Ramp-up Rate                    |                                  | 5°C/second max     |
| Reflow   | Temperature ( $T_L$ ) (Liquidus) | 217°C              |
|  | Temperature ( $t_L$ )            | 60 – 150 seconds   |
| Peak Temperature ( $T_P$ )                             |                                  | 260+0/-5 °C        |
| Time within actual peak Temperature ( $t_p$ )          |                                  | 20 – 40 seconds    |
| Ramp-down Rate   |                                  | 5°C/second max     |
| Time 25°C to peak Temperature ( $T_P$ )                |                                  | 8 minutes Max.     |
| Do not exceed  |                                  | 280°C              |



Outline Drawing –DFN4.1x2-10L

### PACKAGE OUTLINE

**DFN4.1x2-10L**

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN         | MON  | MAX  |
| A   | 0.45        | 0.50 | 0.55 |
| A1  | —           | 0.02 | 0.05 |
| b   | 0.15        | 0.20 | 0.25 |
| c   | 0.10        | 0.15 | 0.20 |
| D   | 4.00        | 4.10 | 4.20 |
| D1  | 0.20        | 0.25 | 0.30 |
| D2  | 1.30        | 1.40 | 1.50 |
| D3  | 0.25        | 0.30 | 0.35 |
| e   | 0.80BSC     |      |      |
| Nd  | 3.20BSC     |      |      |
| E   | 1.90        | 2.00 | 2.10 |
| E2  | 0.70        | 0.80 | 0.90 |
| K   | 0.20        | —    | —    |
| L   | 0.25        | 0.30 | 0.35 |
| h   | 0.15        | 0.20 | 0.25 |

**NOTES:**

- 1.CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING TO ENSURE YOUR COMPANYS MANUFACTURING GUIDELINES ARE MET.

**Marking Codes**

|             |           |              |           |
|-------------|-----------|--------------|-----------|
| Part Number | WE03-6R1N | Marking Code | WE03-6R1N |
|-------------|-----------|--------------|-----------|

**Package Information**

Qty: 3k/Reel

**CONTACT INFORMATION**

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.  
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.  
Users should verify actual device performance in their specific applications.